

THE INVENTION CLAIMED IS

1. A semiconductor device, comprising  
a layer fabricated with pulsed radiation annealing,  
a layer that can be damaged by said pulsed radiation, operatively  
connected to said layer fabricated with pulsed radiation annealing, and  
a reflective layer, operatively connected to said layer that can be  
damaged by said pulsed radiation, for reflecting said pulsed radiation.
2. The semiconductor device of claim 1 wherein said layer that can be  
damaged by said pulsed radiation is low temperature plastic.
3. The semiconductor device of claim 1 wherein said reflective layer is  
single layer or multiple layers for narrowband or broadband reflection.
4. The semiconductor device of claim 3 wherein said reflective layer is a  
narrow band reflectance coating.
5. The semiconductor device of claim 1 wherein said layer fabricated with  
pulsed radiation annealing is fabricated with high intensity radiation sources with a  
short wavelength that will be readily absorbed.

6. The semiconductor device of claim 5 wherein said high intensity radiation sources are pulsed UV excimer lasers, frequency doubled NdYAG lasers, UV flashlamps, or X-ray sources.

7. The semiconductor device of claim 1 wherein said layer fabricated with pulsed radiation annealing is a silicon film that is crystallized by said pulsed radiation annealing.

8. The semiconductor device of claim 1 wherein said layer fabricated with pulsed radiation annealing is a silicon film that is doped by said pulsed radiation annealing.

9. The semiconductor device of claim 1 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation for reflecting said pulsed radiation.

10. The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic, said reflective layer is single layer or multiple layers for narrowband or broadband reflection, and said

layer fabricated with pulsed radiation annealing is fabricated with high intensity radiation sources.

11. The semiconductor device of claim 8 wherein said high intensity radiation sources are pulsed UV excimer lasers, frequency doubled NdYAG lasers, UV flashlamps, or X-ray sources.

12. The semiconductor device of claim 9 wherein said reflective layer is a narrow band reflectance coating.

13. The semiconductor device of claim 10 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation for reflecting said pulsed radiation.